NTE2363 (NPN) & NTE2364 (PNP)
Silicon Complementary Transistors
High Current General Purpose Amp/Switch

Features:
- Low Saturation Voltage
- Large Current Capacity and Wide ASO

Applications:
- Power Supplies
- Relay Drivers
- Lamp Drivers
- Automotive Wiring

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 60V

Collector–Emitter Voltage, V_{CEO} 50V

Emitter–Base Voltage, V_{EBO} 6V

Collector Current, I_C
      Continuous 2A
      Peak 4A

Allowable Collector Dissipation, P_C 1W

Junction Temperature, T_J . . . . +150°C

Storage Ambient Temperature Range, T_{stg} . . . . –55° to +150°C

Note 1 For PNP device (NTE2364), voltage and current values are negative.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 50V, I_E = 0	–	–	0.1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	–	–	0.1	µA
DC Current Gain	h_{FE} (1)	V_{CE} = 2V, I_C = 100mA	140	–	280	
	h_{FE} (2)	V_{CE} = 2V, I_C = 1.5A	40	–	–	
Gain Bandwidth Product	f_T	V_{CE} = 10V, I_C = 50mA	–	150	–	MHz

Electrical Characteristics (Cont'd): (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Capacitance NTE2363	c_{ob}	V_{CB} = 10V, f = 1MHz	–	12	–	pF
NTE2364			–	22	–	pF
Collector–Emitter Saturation Voltage NTE2363	$V_{CE(sat)}$	I_C = 1A, I_B = 50mA	–	0.15	0.4	V
NTE2364			–	0.3	0.7	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 1A, I_B = 50mA	–	0.9	1.2	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10µA, I_E = 0	60	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	50	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10µA, I_C = 0	6	–	–	V